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December 2013

# FQU20N06L

# N-Channel QFET® MOSFET

60 V, 17.2 A, 42 mΩ

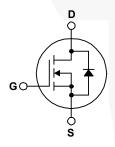
# **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### **Features**

- 17.2 A, 60 V,  $R_{DS(on)}$  = 42 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 8.6 A
- Low Gate Charge (Typ. 9.5 nC)
- · Low Crss (Typ. 35 pF)
- 100% Avalanche Tested
- Low Level Gate Drive Requirements Allowing Direct Operation Form Logic Drivers





# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQU20N06LTU	Unit
$V_{DSS}$	Drain-Source Voltage		60	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		17.2	Α
	- Continuous (T <sub>C</sub> = 100°C)		10.9	Α
I <sub>DM</sub>	Drain Current - Pulsed (	Note 1)	68.8	Α
V <sub>GSS</sub>	Gate-Source Voltage		± 20	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		170	mJ
I <sub>AR</sub>	Avalanche Current (Note 1)		17.2	Α
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)		3.8	mJ
dv/dt	Peak Diode Recovery dv/dt	Note 3)	7.0	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>A</sub> = 25°C) *		2.5	W
	Power Dissipation (T <sub>C</sub> = 25°C)		38	W
	- Derate above 25°C		0.30	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.		300	°C

## **Thermal Characteristics**

Symbol	Parameter	FQU20N06LTU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max. 3.28		
D	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max.	50	

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQU20N06LTU	FQU20N06L	IPAK	Tube	N/A	N/A	70 units

# **Flectrical Characteristics**

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 μA, Referenced to 25°C		0.06		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	-		1	μΑ
		V <sub>DS</sub> = 48 V, T <sub>C</sub> = 125°C	-		10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -20 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1.0		2.5	V
R <sub>DS(on)</sub>	Static Drain-Source	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 8.6 A		0.046	0.06	
20(0)	On-Resistance	$V_{GS} = 5 V, I_D = 8.6 A$			0.075	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 25 V, I <sub>D</sub> = 8.6 A	1	11		S
Dynam	ic Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		480	630	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz	-	175	230	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			35	45	pF
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time			10	30	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 30 \text{ V}, I_D = 10.5 \text{ A},$		165	340	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$R_G = 25 \Omega$		35	80	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		70	150	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 48 V, I <sub>D</sub> = 21 A,	-	9.5	13	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 5 V		2.5		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		5.5		nC
	Source Diede Cheresteriation of	nd Maximum Batinga				
I <sub>S</sub>	Source Diode Characteristics and Maximum Ratings  Maximum Continuous Drain-Source Diode Forward Current				17.2	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				68.8	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage				1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>F</sub> = 21 A,		54		ns
11		dl <sub>F</sub> / dt = 100 A/μs				

Notes: 1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 670  $\mu$ H, I<sub>AS</sub> = 17.2 A, V<sub>DD</sub> = 25 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C. 3. I<sub>SD</sub>  $\leq$  21 A, di/dt  $\leq$  300 A/ $\mu$ s, V<sub>DD</sub>  $\leq$  BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C. 4. Essentially independent of operating tmperature.

# **Typical Characteristics**

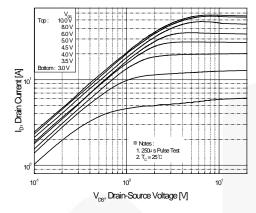


Figure 1. On-Region Characteristics

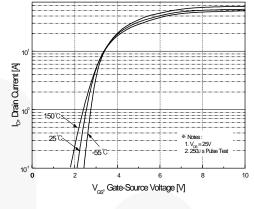


Figure 2. Transfer Characteristics

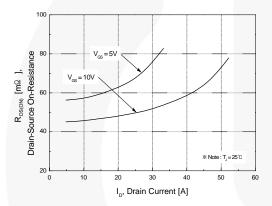


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

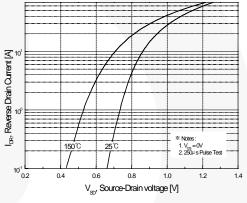


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

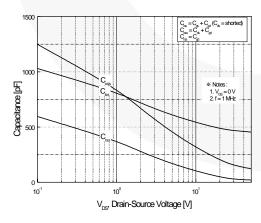


Figure 5. Capacitance Characteristics

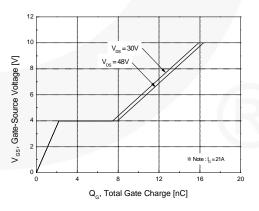


Figure 6. Gate Charge Characteristics

# 1.2 BAN (Water Survey of the state of the s

0.8 L -100

-50

Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

T, Junction Temperature [°C]

100

150

200

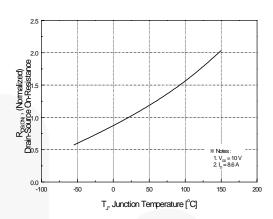


Figure 8. On-Resistance Variation vs. Temperature

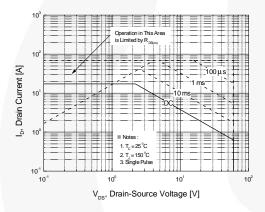


Figure 9. Maximum Safe Operating Area

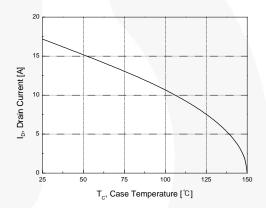


Figure 10. Maximum Drain Current vs. Case Temperature

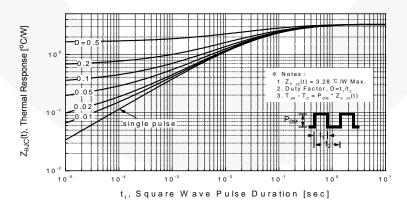


Figure 11. Transient Thermal Response Curve

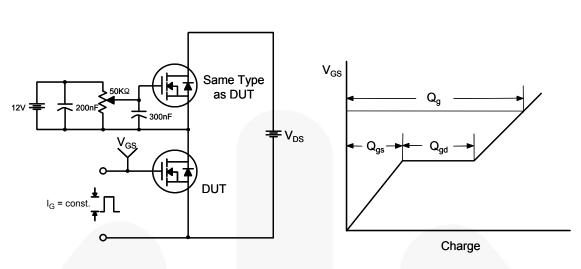


Figure 12. Gate Charge Test Circuit & Waveform

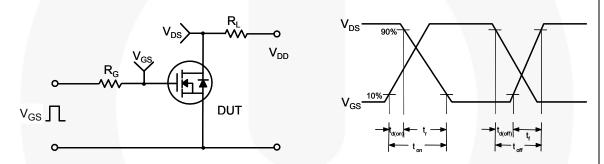


Figure 13. Resistive Switching Test Circuit & Waveforms

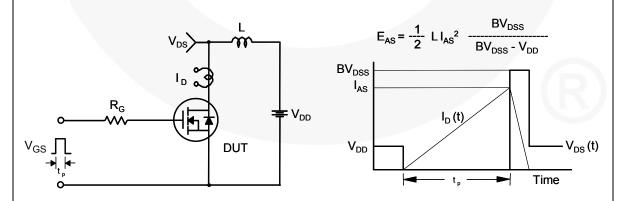
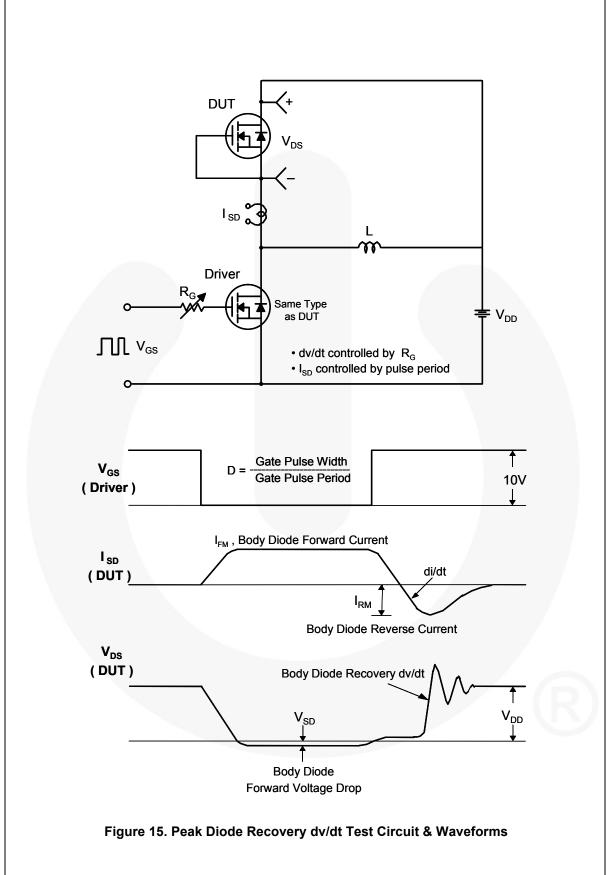


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



# **Mechanical Dimensions**

# FQU13N06LTU

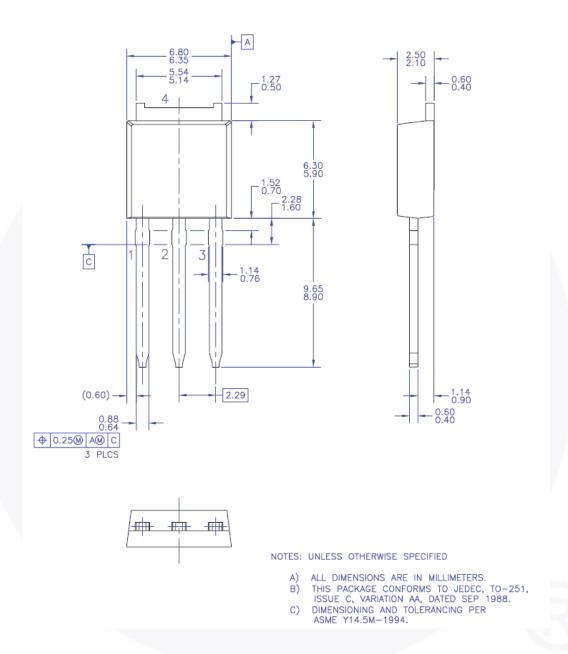


Figure 16. TO251 (I-PAK), Molded, 3-Lead

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